

SANYO Semiconductors DATA SHEET

MCH3221 — NPN Epitaxial Planar Silicon Transistor

DC / DC Converter Applications

Applications

· Relay drivers, lamp drivers, motor drivers, flash.

Features

- · Adoption of MBIT processes.
- · Large current capacitance.
- · Low collector-to-emitter saturation voltage.
- · High-speed switching.
- · Narrow hFE range.
- Ultrasmall package facilitates miniaturization in end products (mounting height: 0.85mm).
- · High allowable power dissipation.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		40	V
Collector-to-Emitter Voltage	VCEO		30	V
Emitter-to-Base Voltage	VEBO		6	V
Collector Current	Ic		3	А
Collector Current (Pulse)	ICP		6	Α
Base Current	IB		600	mA
Collector Dissipation	PC	Mounted on a ceramic board (600mm²X0.8mm)	0.8	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
	Cymbol		min	typ	max	Onne
Collector Cutoff Current	ICBO	VCB=30V, IE=0A			0.1	μΑ
Emitter Cutoff Current	I _{EBO}	V _{EB} =4V, I _C =0A			0.1	μΑ
DC Current Gain	hFE	VCE=2V, IC=500mA	250		400	
Gain-Bandwidth Product	fŢ	V _{CE} =10V, I _C =500mA		450		MHz

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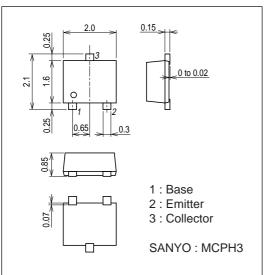
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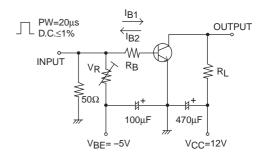
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Output Capacitance	Cob	V _{CB} =10V, f=1MHz		20		pF
Collector-to-Emitter Saturation Voltage	V _{CE} (sat)1	I _C =1.5A, I _B =30mA		80	120	mV
	VCE(sat)2	IC=1.5A, IB=75mA		65	100	mV
Base-to-Emitter Saturation Voltage	V _{BE} (sat)	IC=1.5A, IB=30mA		0.83	1.2	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	I _C =10μA, I _E =0A	40			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	IC=1mA, RBE=∞	30			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E =10μA, I _C =0A	6			V
Turn-ON Time	ton	See specified Test Circuit.		30		ns
Storage Time	tstg	See specified Test Circuit.		300		ns
Fall Time	tf	See specified Test Circuit.		15		ns

Package Dimensions

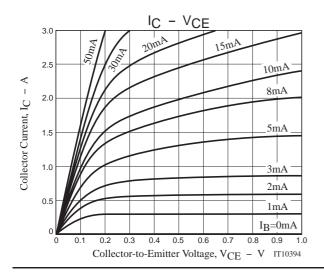
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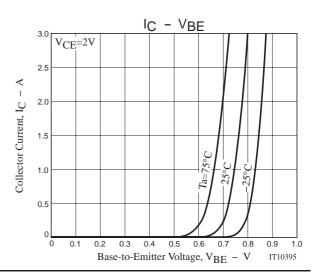


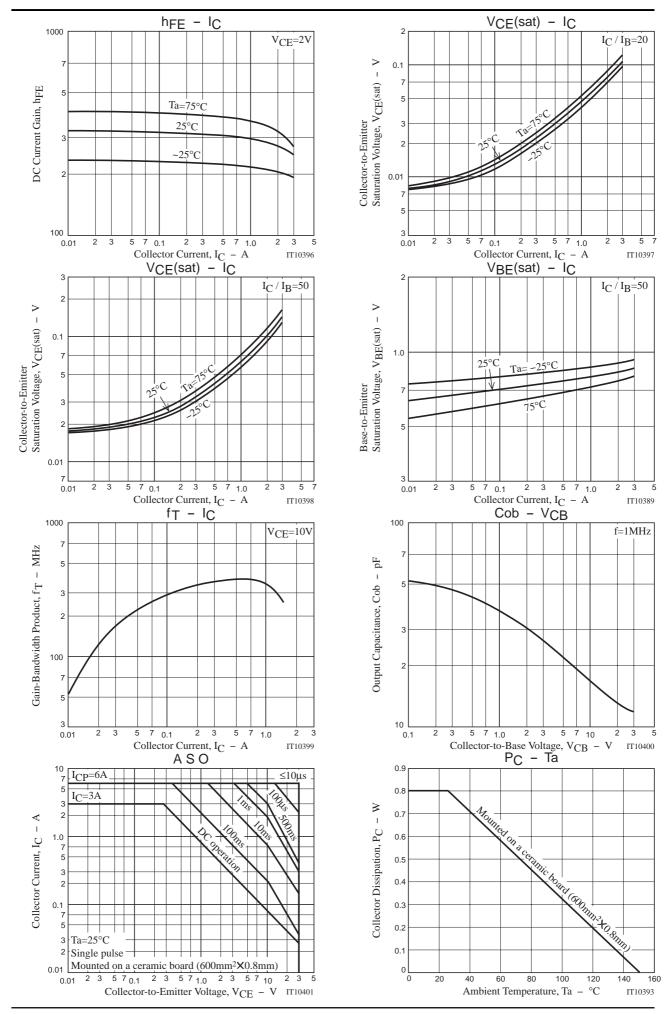
Switching Time Test Circuit



$$I_{C}=20I_{B1}=-20I_{B2}=500mA$$







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